

ABSTRACT OF THE DISCLOSURE

A phase-shifting mask for a photolithographic process includes a transparent material having first and second trenches. The first trench has a first depth and the second trench has a second depth deeper than the first depth. The phase-shifting mask is suitable for testing the effect of lights of two wavelengths on a layer of photoresist.

001.1100862.1

INDUSTRIAL DESIGN
REGISTRATION
NUMBER
20552